

# Compact Ultra-Efficient Solar/Light Energy Harvesting Battery Charger

## **Benefits and Features**

#### Ultra-low power startup:

- Cold start from 250 mV input voltage and 5  $\mu$ W input power (typical).

#### Highly efficient energy extraction:

- Periodic open-circuit voltage sensing for Maximum Power Point Tracking (MPPT);
- Configurable MPPT ratios of 35, 50 and from 60 to 90% by 5% steps;
- Constant impedance matching (QFN package only);
- Configurable MPPT sensing timing and period;
- MPPT voltage operation range from 115 mV to 1.5 V.

#### Flexible energy storage management:

- Selectable overdischarge protection from 2.8 V to 4.0 V;
- Selectable overcharge protection from 3.0 V to 4.8 V;
- For any type of rechargeable battery;
- Battery charge can be disabled, e.g. during transportation.

#### Configuration and communication:

- Static configurations available through configuration pins (depending on package) or I<sup>2</sup>C interface;
- I<sup>2</sup>C interface to set system functionalities and read system information;
- I<sup>2</sup>C mode up to Fast Mode Plus.

#### Configurable thermal protection:

- From -40°C to 125°C with accuracy below 1.5°C up to 60°C.

#### Power meter:

- Energy transfer or pulse counter mode.

#### Smallest footprint, smallest BOM:

- WLCSP16-pin 2x2 mm or QFN 28-pin 4x4mm;
- Only three passive components.

## Applications



## Description

The AEM10900 is a fully integrated and compact battery charger circuit that extracts DC power from a harvester to store energy in a rechargeable battery. This compact and ultra-efficient battery charger allows to extend battery lifetime and eliminates the primary energy storage in a large range of wireless application, such as wearable and medical applications, asset tracking and IoT Sensors.

Thanks to its Maximum Power Point Tracking and its ultra-low power boost converter, the AEM10900 harvests the maximum available input power from a source to charge a storage element, such as a Li-ion battery. The boost converter operates with input voltages in a range from 115 mV to 1.5 V.

With its unique cold-start circuit, it can start operating with an input voltage as low as 250 mV and an input power of only 5  $\mu$ W. The output voltages are in a range of 2.8 V to 4.8 V.

The configurable protection levels determine the storage element voltage protection thresholds to avoid overcharging and overdischarging the storage element and thus damaging it. Those levels are set without requiring any external component.

It implements thermal monitoring for battery protection, as well as an average power monitoring system (APM) which allows the application circuit to get a measure of harvested energy.

The AEM10900 internal circuitry can be supplied either from the source or from the battery ("Keep alive" functionality). Being supplied from the battery avoids the need of a cold start after a period with no energy available on the source. On the other hand, when supplied only from the source an always positive power balance is guaranteed even if energy harvesting is not occurring for long periods of time.

It is optimal for wearable applications with its small footprint and small BOM (two capacitors and one inductor). All parameters can be set through an I<sup>2</sup>C interface, such as thermal shutoff, battery monitoring and MPPT, allowing more flexibility to customer designs.

## **Device Information**

Package	Body size [mm]
WLCSP16-pin	2x2mm
QFN 28-pin	4x4mm

## **Evaluation Board**

Part number 2AAEM10900C001



## **Table of Contents**

1. Introduction	6
2. Absolute Maximum Ratings	9
3. Thermal Resistance	9
4. Typical Electrical Characteristics at 25 °C	9
5. Recommended Operation Conditions	10
6 Functional Block Diagram	
7 Theory of Operation	12
7.1 Poort Convertor	12
7.1. BOOST CONVERTER	12
7.2. Thermal Monitoring	12
7.5. Merinal Monitoring	13
7.5. Automatic High Power Mode	13
7.6. Keen-alive	13
7.7. State description	
7.7.1 Reset State	13
7.7.2.Sense SRC State	
7.7.3.Sense STO State	
7.7.4. Supply State	
7.7.5.Sleep State	
8. System Configuration	14
8.1. Configuration Pins and I <sup>2</sup> C	14
8.2. MPPT Configuration	15
8.3. ZMPP Configuration	15
8.4. Storage Element Thresholds Configuration	16
8.5. I <sup>2</sup> C Serial Interface	16
8.6. Registers Map	
8.7. Registers Configurations	19
8.7.1.MPPT Register	19
8.7.2.Storage Element Threshold Registers	19
8.7.3.Temperature Register	19
8.7.4.Power Register	19
8.7.5.Sleep Register	20
8.7.6.Acquisition of STO Register	20
8.7.7.APM Register	20
8.7.8.IRQEN Register	
8.7.9.Control Register	
8.7.10.IRQFLG Register	
8.7.11.STATUS Register	
8.7.12.APM Data Register	
8.7.13.1 emperature data Register	
8.7.14.Battery data Register	
8.7.15.5KU Kegister	
8.8. External Components	25



8 8 1 Storage element	25
8 8 2 External inductor information	25
9.9.2 External capacitors information	25
	25
8.8.4. Optional external component for thermal monitoring	25
8.8.5.Optional pull-up resistors for the I <sup>2</sup> C interface	25
9. Typical Application Circuits	26
9.1. Example Circuit 1	.26
9.2. Example Circuit 2	.27
	.28
10. Performance Data	31
10.1. DCDC Conversion Efficiency	.31
10.2. Quiescent Current	.31
11. Package Information	32
11.1. Wafer Level Chip Scale Package (WLCSP16 2x2mm)	.32
11.2. WLCSP16 Board Layout	.32
11.3. Plastic quad flatpack no-lead (QFN28 4x4mm)	.33
11.4. QFN28 Board Layout	.33
11.5. Minimum BOM	.34
12. Revision History	35



# **List of Figures**

Figure 1: Simplified schematic view	6
Figure 2: Pinout diagram WLCSP16	7
Figure 3: Pinout diagram QFN28	8
Figure 4: Functional block diagram (WLCSP16 package)	11
Figure 5: Simplified schematic view of the AEM10900	12
Figure 6: TH_REF and TH_MON connections	13
Figure 7: Diagram of the AEM10900 state	13
Figure 8: I <sup>2</sup> C transmission frame	16
Figure 9: Read and write transmission	17
Figure 10: Typical application circuit 1	26
Figure 11: Typical application circuit 2	27
Figure 12: Start-up State	28
Figure 13: Supply State	28
Figure 14: Behavior with the Keep Alive mode and without the source	29
Figure 15: Behavior without the Keep Alive mode and without the source	29
Figure 16: Thermal Monitoring Behavior	30
Figure 17: DCDC Conversion Efficiency (LDCDC: VLS252012HBX-4R7M-1)	31
Figure 18: Quiescent Current	31
Figure 19: WLCSP16 2x2mm	32
Figure 20: WLCSP16 board layer	32
Figure 21: QFN28 4x4 mm	33
Figure 22: QFN28 4x4 mm board layout	33
Figure 23: AEM10900 schematic	34



## **List of Tables**

Table 1: Pins description WLCSP16	7
Table 2: Pins description QFN28	8
Table 3: Absolute maximum ratings	9
Table 4: Thermal data	9
Table 5: Electrical characteristics	9
Table 6: Recommended operating conditions	10
Table 7: Configuration of MPP ratio	15
Table 8: Configuration of MPP timing	15
Table 9: Usage of CFG[2:0]	16
Table 10: Register summary	18
Table 11: PWR Register	19
Table 12: SLP register	20
Table 13: Configuration of the sleep threshold	20
Table 14: Acquisition rates for STO ADC	20
Table 15: APM register	20
Table 16: Configuration of APM computation windows	20
Table 17: IRQEN register	21
Table 18: CTRL register	21
Table 19: IRQFLG register.	21
Table 20: CTRL register    20: CTRL register	22
Table 21: APMx registers in pulse counter mode	22
Table 22: APMx registers in pulse counter mode	22
Table 23: Source regulation configuration pins	24
Table 24: AEM10900 bill of material	34



Figure 1: Simplified schematic view

## 1. Introduction

The AEM10900 is a full-featured energy efficient battery charger able to charge a storage element (connected to STO) from an energy source (connected to SRC).

The core of the AEM10900 is a regulated switching converter (boost) with high-power conversion efficiency.

At first start-up, as soon as a required coldstart voltage of 250 mV and a sparse amount of power of at least 5  $\mu$ W is available at the source, the AEM10900 coldstarts. After the cold start, the AEM extracts the power available from the source if the input voltage is higher than 115mV.

The AEM10900 can be fully configured through the  $I^2C$  interface or partially by configuration pins (depending on the package).  $I^2C$  configuration is not mandatory, as the default configuration is made to fit the most common needs, along with the configuration pins for the most common settings (depending on the package).

Through  $I^2C$  communication or through the configuration pins, the user can select a specific operating mode from a variety of modes that cover most application requirements without any dedicated external component. The battery protection thresholds ( $V_{OVCH}$  and  $V_{OVDIS}$ ) have a default value. They can also be configured in 60 mV steps using the  $I^2C$  bus or the configuration pins STO\_CFG[2:0] (QFN28 package only).

The Maximum Power Point (MPP) ratio is configurable by the configuration pins (R\_MPP[2:0] on QFN28 package, R\_MPP[0] on WLCSP16) or by the I<sup>2</sup>C interface. It ensures an optimum biasing of the harvester to maximize power extraction. The user can select a specific MPP ratio from two values (WLCSP16 package) or from eight values (QFN28 package), set by the configuration pins. With the I<sup>2</sup>C interface, the user

can select a ratio amongst 9 different values.

Depending on the harvester, it is possible to adapt the timing between two MPP evaluations and the open circuit duration with the  $I^2C$  communication but also with the configuration pins T\_MPP[1:0] for the QFN28 version. There is a range of eight timing pairs.

AEM10900 features an optional temperature protection. It is set through the  $I^2C$  interface and allows to define a temperature range outside which the battery will not be charged by the boost converter. One additional resistor and one additional thermistor are needed for this feature

The KEEP ALIVE functionality sets the source to supply the AEM10900 internal circuitry VINT, which can be supplied either from the harvester connected on SRC or from the battery connected to STO. When supplied by SRC, the AEM10900 internal circuitry is running as long as enough energy is available on SRC. If no energy available on SRC, the internal voltage drops until reset voltage and the AEM needs to go through a cold start before being able to charge the battery again. This is useful for applications with long periods without energy on SRC and when the I<sup>2</sup>C is not used. With this setting there is no quiescent current taken from the battery to supply the AEM10900 and the power balance is always positive. When supplied by STO, the circuit stays in SUPPLY STATE or SLEEP STATE as long as the battery connected to STO is above the over-discharge threshold. It prevents loosing the I<sup>2</sup>C configuration when energy harvesting is not occurring while minimizing the leakage on the battery.

The AEM10900 prevent the charging of the battery on STO, when the environment conditions does not allow to charge it safely thanks to the thermal monitoring.



#### Figure 2: Pinout diagram WLCSP16

NAME	PIN NUMBER	Function		
Power pins				
SRC	A4	Connection to the harvested energy source.		
BUFSRC	B4	Connection to an external capacitor buffering the boost converter input.		
SWDCDC	C4	Switching node of the boost converter.		
VINT	C3	Internal voltage supply.		
I2C_VDD	C2	Connection to I <sup>2</sup> C supply voltage. Connect to GND if not used.		
STO	D4	Connection to the energy storage element (battery).		
510	D4	Cannot be left floating, voltage must always be above 2.8 V.		
l <sup>2</sup> C pins				
SDA	D1	Bidirectional data line. Connect to I2C_VDD if not used.		
SCL	C1	Unidirectional serial clock for I <sup>2</sup> C. Connect to I2C_VDD if not used.		
IRQ	D2	Output Interrupt request. Left floating if not used.		
		Configuration bit for I <sup>2</sup> C address. Read as high if left floating.		
I2C_ADDRB1If set high, the address is 0x41.If set low, the address is 0x40		If set high, the address is 0x41.		
		If set low, the address is 0x40		
Configuration pins				
TH_REF	A3	Reference voltage for thermal monitoring. Leave floating if not used.		
TH_MON	A2	Pin for temperature monitoring. Connect to VINT is not used.		
R_MPP[0]	B2	Used for the configuration of the MPP ratio. Read as high if left floating.		
Control pins				
DIS_STO_CH	D3	When asserted, the AEM stops charging the battery. Read as low if left floating.		
Other pins				
GND	A1, B3	Ground connection, both terminals should be strongly tied to the PCB ground plane.		

Table 1: Pins description WLCSP16





Figure 3: Pinout diagram QFN28

NAME	PIN NUMBER	Function	
Power pins	•		
SRC	28	Connection to the harvested energy source.	
BUFSRC	3	Connection to an external capacitor buffering the boost converter input.	
SWDCDC	5	Switching node of the boost converter.	
VINT	6, 18	Internal voltage supply.	
STO	8	Connection to the energy storage element (battery). Cannot be left floating, voltage must always be above 2.8 V.	
I2C_VDD	10	Connection to supply I <sup>2</sup> C interface. Connect to GND if I <sup>2</sup> C is not used.	
ZMPP	27	Connection for the ZMPP (Must be left floating when not used)	
I <sup>2</sup> C pins	1		
SDA	13	Bidirectional data line. Connect to I2C_VDD if not used.	
SCL	12	Unidirectional serial clock for I <sup>2</sup> C. Connect to I2C_VDD if not used.	
IRQ	11	Output Interrupt request. Leave floating if not used.	
Configuration pins			
STO_CFG[0]	19	lised for the configuration of the threshold voltages for the energy storage	
STO_CFG[1]	17	element Read as high if left floating	
STO_CFG[2]	22		
T_MPP[0]	16	Used for the configuration of the MPP timings Read as high if left floating	
T_MPP[1]	21	osea for the comparation of the twill annugs. Nead as high infere noathig.	
R_MPP[0]	20		
R_MPP[1]	15	Used for the configuration of the MPP ratio. Read as high if left floating.	
R_MPP[2]	24		
TH_REF	26	Reference voltage for thermal monitoring. Leave floating if not used.	
TH_MON	25	Pin for temperature monitoring. Connect to VINT if not used.	
Control pins			
DIS_STO_CH	9	When high, the AEM stops charging the battery. Read as low if left floating.	
KEEP_ALIVE	14	When high, the internal circuitry is supplied from STO. When low, the internal circuitry is supplied from SRC.	
Other pins	-		
GND	1, 4, 23,back plane	Ground connection, each terminal should be strongly tied to the PCB ground plane.	
NC	2, 7	Not connected pins, leave floating.	

Table 2: Pins description QFN28



## 2. Absolute Maximum Ratings

Parameter	Value
Voltage on SRC	2V
Voltage on STO	5.5V
Operating junction temperature	-40°C to 125°C
ESD HBM voltage	TBD
ESD CDM voltage	TBD

Table 3: Absolute maximum ratings

## **3. Thermal Resistance**

Package	ALθ	θͿϹ	Unit
WLCSP16	TBD	TBD	°C/W
QFN28	TBD	TBD	°C/W

Table 4: Thermal data

ESD CAUTION

ESD (ELECTROSTATIC DISCHARGE) SENSITIVE DEVICE These devices have limited built-in ESD protection and

These devices have limited built-in ESD protection and damage may thus occur on devices subjected to high-energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality

## 4. Typical Electrical Characteristics at 25 °C

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Power Conversion	1					
Perces	Source power required for cold start	During cold start KEEP_ALIVE = V <sub>INT</sub>		5		μW
· SRC,CS		During cold start KEEP_ALIVE = GND		14		μW
V <sub>SRC</sub>	Input voltage of the energy source to enable harvesting		0.250		1.5	V
RMPP	MPPT ratio			See Table 8	3	%
V <sub>MPP</sub>	Regulation voltage on SRC when extraction	ing power.	0.115	V <sub>OC</sub> x RMPP	1.5	V
V <sub>SRC,REG</sub>	Regulation voltage of the source		Depends on SRC	C_LVL_CFG[	5:0] configuration	V
V <sub>OC</sub>	Open-circuit voltage of the source	-		1.5	2.0	V
Timing						
T <sub>SRC</sub>	Open-circuit duration for the MPP evalu	ations			)	ms
T <sub>MPPT</sub>	Time between two MPP evaluations			See Table S	)	S
Storage element						
V <sub>STO</sub>	Voltage on the storage element		2.81		4.78	V
V <sub>OVCH</sub>	Maximum voltage accepted on the stor disabling its charging	3	See	4.78	V	
V <sub>OVDIS</sub>	Minimum voltage accepted on the storage element before stopping to supply VINT if Keep-alive is enabled.		2.81	8.4	4.05	V
Internal supply &	Quiescent Current					
V <sub>INT</sub>	Internal voltage supply			2.2		V
I <sub>QSUPPLY</sub>	Quiescent current on VINT in SUPPLY STATE	V <sub>STO</sub> = 3.7 V		300		nA
I <sub>QSLEEP</sub>	Quiescent current on VINT in SLEEP STATE	V <sub>STO</sub> = 3.7 V		150		nA
I <sub>QSTO</sub>	Quiescent current on STO when Keep- alive functionality is disabled			1		nA
T <sub>RESET,SLEEP</sub>	Delay before reset when no energy on SRC and Keep-alive functionality disabled. or if Keep-alive is enabled but	CINT = 3.3 µF (leakage AEM in SLEEP STATI communication	ge neglected), E, no I <sup>2</sup> C	2.2		S
T <sub>RESET,SUPPLY</sub>	the battery voltage dropped below Vovdis	CINT = 3.3 µF (leaka AEM in SUPPLY STA communication	ge neglected), TE, no l <sup>2</sup> C	1.1		S

Table 5: Electrical characteristics



## **5. Recommended Operation Conditions**

Symbol	Parameter			Тур	Max	Unit	
External Component	S						
LDCDC	Inductor of the boost converter		3.3	4.7	6.8	μH	
CSRC	Capacitor decoupling the BUFSRC terminal		10			μF	
CINT	Capacitor decoupling the internal voltage		3.3			μF	
RZMPP	Optional - Resistor for the ZMPPT configuration (s	ee page 25)	33		1M	Ohm	
Rdiv	Optional - pull-up resistor for the thermal monito	ring	5k	22k	33k	Ohm	
Pth	<b>Ontional</b> - thermistor for the thermal monitoring	RO		10k		Ohm	
IXUI I		Beta		3380		K	
Rscl	<b>Optional</b> - pull-up resistors for the $l^2C$ interface			11/2		Ohm	
Rsda				TK		Unin	
Logic input pins							
	Configuration pips for the MPP ratio	Logic high	Connect to VINT				
N_WH 1 [2.0]	computation pins for the wire facto	Logic low	Connect to GND				
	Configuration nins for the MPP timings	Logic high	Connect to VINT				
1_10111[1:0]	configuration pins for the wirt tinnings	Logic low	Connect to GND				
	Configuration pins for the storage element	Logic high	Connect to VINT				
510_616[2:0]	thresholds	Logic low	Connect to GND				
KEED VIIVE	Configuration for the "Keen alive" functionality	Logic high	Connect to VINT				
	comparation of the keep anye functionality	Logic low		Connect to GND			
DIS STO CH	DIS_STO_CH Configuration for disabling the charging of the battery Logic low		Connect to STO				
DI5_510_CI1			Connect to GND				
I <sup>2</sup> C interface pins							
I2C_VDD	I <sup>2</sup> C interface supply pin		1.5		V <sub>STO</sub>	V	
SCL	I <sup>2</sup> C interface communication ninc		Dull up to I2C VDD with resistors				
SDA				run-up to ize_voo with resistors			

Table 6: Recommended operating conditions





## 6. Functional Block Diagram



Figure 4: Functional block diagram (WLCSP16 package)





Figure 5: Simplified schematic view of the AEM10900

## 7. Theory of Operation

### 7.1. Boost Converter

The boost (step-up) converter raises the voltage available at BUFSRC to a level suitable for charging the storage element, in the range of 2.81 V to 4.78 V, according to the system configuration. The switching transistors of the boost converter are M2, M3 and M4. The reactive power component of this converter is the external inductor LDCDC.

Periodically, the MPP control circuit disconnects SRC and BUFSRC pins (transistor M1) in order to measure the opencircuit voltage of the harvester and evaluate the input target voltage. BUFSRC is decoupled by the capacitor CSRC, which smooths the voltage against the current pulses induced by the boost converter.

The storage element is connected to the STO pin, which voltage is V<sub>STO</sub>. This node is linked to the output of boost converter through transistor M4. When energy harvesting is occurring the boost converter charges the battery. M4 disconnects the storage element when V<sub>STO</sub> reaches V<sub>OVCH</sub>. If VINT drops below its regulation value and if Keep-alive functionality is disabled, the AEM switches its output by

enabling M3 instead of M4 until VINT reaches its target plus a small hysteresis. If the Keep-alive functionality is enabled, VINT is instead supplied from STO by modulating the gate of M5. In this case M3 is never activated.

### 7.2. Maximum Power Point Tracking

During SUPPLY MODE, SENSE SRC MODE or SENSE STO MODE the voltage on SRC is regulated by an internal MPPT (Maximum Power Point Tracking) module. The MPPT module evaluates V<sub>MPP</sub> as a constant fraction of V<sub>OC</sub> (open-circuit voltage of the source). This ratio is set by the I<sup>2</sup>C interface or with the configuration pins according to table 7. The sampling period and duration of the V<sub>OC</sub> are set according to table 8 by configuring of the T\_MPP[1:0] field in the MPP register or with the configuration pins. The AEM10900 supports any V<sub>MPP</sub> levels in the range from 115 mV to 1.5 V. It offers a choice of up to nine values for the V<sub>MPP</sub> / V<sub>OC</sub> fraction. To maximize the power extraction from the harvester, the user must select the V<sub>MPP</sub> / V<sub>OC</sub> ratio according to the harvester specifications.



## 7.3. Thermal Monitoring

Thermal monitoring allows to protect the storage element. Enabling this functionality requires the use of a resistor (Rdiv) and a thermistor (Rth). See figure 6 for external components connections. The TH\_REF terminal allows a reference voltage to be applied to the resistive divider while TH\_MON is the measuring point. The temperature evaluation is done periodically (typ. every 8 s) to spare power. Information for the thermal monitoring is described in section 8.7.3. Thermal monitoring is optional, if not used connect TH\_MON to VINT and leave TH\_REF floating.



Figure 6: TH\_REF and TH\_MON connections

## 7.4. Average Power Monitoring

The Average Power Monitoring (APM) allows to evaluate the energy transfer from SRC to STO. The APM is able to determine the transferred energy by counting the number of current pulses transferred to STO by the boost converter over a configurable time window, and thus roughly evaluate the corresponding energy.

There are two modes available. The first one allows to recover the number of current pulses and the second one the energy that is transferred by the AEM.

Refer to section 8.7.7. for further details.

### 7.5. Automatic High Power Mode

Automatic high-power mode allows higher currents to be extracted from SRC to STO through the boost converter. When the AEM10900 detects that the energy available on SRC is high enough, the boost converter automatically switches to high-power mode. While higher currents can be extracted from SRC in this mode, the efficiency is lower.

It might be useful to prevent switching to high-power mode for batteries sensitive to the charging current level. This feature is enabled by default and can be disabled by setting the PWR.HPEN to 0 through the  $\rm I^2C$  interface.

### 7.6. Keep-alive

The internal circuitry connected to VINT can be supplied either by SRC through the boost converter (Keep-alive disabled), or by the battery STO (Keep-alive enabled).

When supplied from SRC, the AEM10900 switches to RESET STATE when the energy available on SRC is not sufficient. The advantage is that no energy is pulled from the battery when the AEM10900 is not harvesting energy from SRC. The drawback is that the AEM has to cold start after every period without enough energy on SRC.

When supplied from STO, VINT is regulated as long as enough energy is available from the battery on STO, thus avoiding having to cold start if the energy on SRC is not constant.

### 7.7. State description

#### 7.7.1. Reset State

In RESET STATE all nodes are deeply discharged and there is no available energy to be harvested. The AEM stays in this state until the source connected to SRC meets the coldstart requirements (V<sub>SRC</sub> above 250 mV and P<sub>SRC,CS</sub> above 5  $\mu$ W). VINT then rises to 2.2 V, and the AEM switches to SENSE SRC STATE.



Figure 7: Diagram of the AEM10900 state



#### 7.7.2. Sense SRC State

In SENSE SRC STATE, the AEM10900 reads the configuration pins and does a first MPPT to evaluate the power available at SRC. The MPPT is described in section 7.2.

The next step is therefore to determine whether the battery can be charged. This mode is called SENSE STO STATE.

#### 7.7.3. Sense STO State

In SENSE STO STATE the AEM10900 does the following measurements, then switches to SUPPLY STATE:

Battery voltage on STO;

Temperature through pins TH\_MON and TH\_REF (see section 7.3. and 8.7.3.).

#### 7.7.4. Supply State

In SUPPLY STATE, the AEM transfers charges directly from SRC to STO while maintaining  $V_{\rm INT}$ .

If  $V_{INT}$  drops and the energy available on SRC is not sufficient

## 8. System Configuration

### 8.1. Configuration Pins and I<sup>2</sup>C

After a cold start, the AEM10900 reads the configuration pins. Those are then read periodically every 2 s, with the exception of the DIS\_STO\_CH pin that is read every 1 s. The configuration pins can be changed on-the-fly. The floating configuration pins are read as 1, excepted DIS\_STO\_CH which is read as 0.

To configure the AEM10900 through the I<sup>2</sup>C interface, user must write to the desired registers and validate the configuration by setting the CTRL.UPDATE. The configuration pins are then ignored and all the configurations are set by the to make  $V_{INT}$  rise again, there are two possible behaviors, depending on the 'Keep Alive' feature:

If 'Keep alive' is enabled, Vint is supplied by the battery through M5, so the AEM10900 stays in SUPPLY STATE while energy is available on the battery;

If 'Keep alive' is disabled, the AEM internal circuitry will no longer be maintained and the AEM switches to RESET STATE.

#### 7.7.5. Sleep State

of the AEM10900.

In SLEEP STATE, the AEM power consumption is reduced, since the power on the input is presumably low ( $V_{SRC}$  below the threshold voltage defined by the SLEEP.THRESH filed). If the source voltage rises again or if the SLEEP.EN field is set to 0, the AEM10900 switches back to SUPPLY STATE. SLEEP STATE entering or exiting is triggered by the MPP acquisitions. SLEEP STATE is enabled by default with a 105 mV threshold. It is not recommended to disable SLEEP STATE for standard uses

register values. All registers have a default value.

Please note that before sending the first I<sup>2</sup>C command after the AEM10900 is in RESET STATE, the user must make sure that the IRQ pin is high, notifying that the I<sup>2</sup>C interface is ready (see section 8.7.8.).

When using the I<sup>2</sup>C configuration, it is highly recommended to enable the Keep-alive functionality (see section 8.7.4.) in order to avoid losing the register configuration if no energy is available on SRC.



### 8.2. MPPT Configuration

Two parameters are necessary to configure the Maximum Point Tracking. The first parameter is the MPP tracking ratio, which is selected according to the characteristics of the input power source. This parameter is set on bits [3:0] of the MPPT\_CFG (0x01) register, or by the configuration pins for the QFN28 package. On the WLCSP16 package, only R\_MPP[0] is available as a configuration pin. The second parameter allows configuring the duration of the evaluation of  $V_{OC}$  and the time between two MPP evaluations. The configuration is set on bits [6:4] of the MPPT\_CFG (0x01) register, or by the configuration pins for the QFN28 package.

Configuration	Avail	MPPT ratio		
	l²C	Configura	Vmpp/Voc	
K_IVIPP[5.0]	Interface	QFN28	WLCSP16	
0000	yes	yes	no	ZMPP
0001	yes	yes	no	90%
0010	yes	yes	no	65%
0011	yes	yes	no	60%
0100	yes	yes	no	85%
0101	yes	yes	no	75%
0110	yes	yes	yes	70%
0111	yes	yes	yes	80%
1000	yes	no	no	35%
1001	yes	no	no	50%

Table 7: Configuration of MPP ratio

Configuration	Avail	ability Through	n Pins	MPP Timing		
	l²C	Configuration pins		Sampling duration	Sampling period	
1_101FF[2.0]	Interface	QFN28	WLCSP16	[ms]	[ms]	
000	yes	no	no	2	64	
001	yes	no	no	256	16384	
010	yes	no	no	64	4096	
011	yes	no	no	8	1024	
100	yes	yes	no	4	256	
101	yes	yes	no	2	128	
110	yes	yes	no	4	512	
111	yes	yes	yes	2	256	

Table 8: Configuration of MPP timing

### 8.3. ZMPP Configuration

Instead of working at a ratio of the open-circuit voltage, the AEM10900 can regulate the input resistance of the boost converter so that it matches a constant resistance connected

to the ZMPP pin (RZMPP). In this case, the AEM10900 regulates  $V_{SRC}$  at a voltage equal to the product of the ZMPP resistance and the current available at the SRC input.



### 8.4. Storage Element Thresholds Configuration

It is possible to set the voltage thresholds for which the storage element is considered to be discharged (V<sub>OVDIS</sub>) and fully charged (V<sub>OVCH</sub>).

 $V_{\text{OVDIS}}$  is configured on the VOVDIS (0x02) register and encoded on 6 bits. The value to be written to the register is determined using the following equation:

$$\text{THRESH} = \frac{V_{OVDIS} - 0.50625}{0.05625}$$

THRESH is the integer value to be written in the register. The minimum value is 2.8 V. If the register value corresponds to

 $V_{OVDIS}$  < 2.8 V, the threshold voltage is forced to 2.8 V.

 $V_{OVCH}$  is configured on the VOVCH (0x03) register and encoded on 6 bits. The value to be written to the register is determined using the following equation:

THRESH = 
$$\frac{V_{OVCH} - 1.2375}{0.05625}$$

THRESH is the integer value to be written in the register. The minimum value is 3.0 V. If the register value corresponds to  $V_{OVCH}$  < 3.0 V, the threshold voltage is forced to 3.0 V.

On the QFN28 package, it is also possible to configure V\_{OVDIS} and V\_{OVCH} with configuration pins STO\_CFG[2:0] as shown in table 9.

Configuration	Availability Through Pins			Storage element threshold voltage		
STO CEC[2:0]	l²C	Configuration pins		V	V	
310_CFG[2.0]	Interface	QFN28	WLCSP16	V OVCH	VOVDIS	
000	yes	yes	no	4.50 V	3.30 V	
001	yes	yes	no	4.00 V	2.80 V	
010	yes	yes	no	3.63 V	2.80 V	
011	yes	yes	no	3.90 V	2.80 V	
100	yes	yes	no	3.90 V	3.50 V	
101	yes	yes	no	3.90 V	3.01 V	
110	yes	yes	no	4.35 V	3.01 V	
111	yes	yes	yes	4.12 V	3.01 V	

Table 9: Usage of CFG[2:0]

## 8.5. I<sup>2</sup>C Serial Interface

The AEM10900 uses I<sup>2</sup>C communication for configuration as well as to provide information about system status and measurement data. Communication requires a serial data line (SDA) and a serial clock line (SCL). A device sending data is defined as a transmitter and a device receiving data as a receiver. The device that controls the communication is called a master and the device it controls is defined as the slave.



Figure 8: I<sup>2</sup>C transmission frame

The master is in charge of generating the clock, managing bus accesses and generating the start and stop bits. The AEM10900 is a slave that will receive configuration data or send the informations requested by the master.

The AEM10900 supports I<sup>2</sup>C Standard-mode (100 kHz maximum clock rate), Fast-mode (400 kHz maximum clock rate), and Fast-mode Plus (1 MHz maximum clock rate) device. Data are send with the most significant bit first.

Here are some typical I<sup>2</sup>C interface states:

- When the communication is idle, both transmission lines are pulled-up (SDA and SCL are open drain outputs);
- Start bit (S): to initiates the transmission, the master switches the SDA line low while keeping SCL high. This is called the start bit;
- Stop bit (P): to end the transmission, the master switches the SDA line from low to high while keeping SCL high. This is called a stop bit;
- Repeated Start bit (Sr): it is used as a back-to-back start and stop bit. It is similar to a start condition, but when the bus is not on idle;
- ACK: to acknowledge a transmission, the device receiving the data (master in case of a read mode transmission, slave in case of a write mode transmission) switches SDA low;
- NACK: when the device receiving data keeps SDA high after the transmission of a byte. When reading a byte, this can mean that the master is done reading bytes from the slave.



To initiate the communication, the master sends a byte with the following informations:

- Bits [7:1] is the slave address, which is 0x40 or 0x41 for the AEM10900, depending on the value of the I2C\_ADDR pin. For packages where the I2C\_ADDR pin is not present, the address is 0x41;
- Bit [0] is the communication mode: 1 for 'read mode' (used when the master reads informations from the slave) and 0 for 'write mode' (when the master writes informations to the slave);
- Slave replies with an ACK to acknowledge that the address has been successfully transmitted.

Here is the procedure for the master to write a slave register:

- Master sends the address of the slave in 'write' mode;
- Slave sends an ACK;
- Master sends the address of the register to be written. For example, for the TEMPCOLD register, the master sends the value 0x04;
- Slave sends an ACK;
- Master sends the data to write to the register;
- Slave sends an ACK;
- If the master wants to write register at the next address (TEMPHOT in our example), it sends next value to write, without having to specify the address again. This can be done several times in a row for

writing several registers;

- Else the master sends a stop bit (P).

Here is the procedure for the master to read a slave register:

AEM10900

Master sends the address of the slave in 'write' mode;

Slave sends an ACK;

Master sends the address of the register to be read. For example, for the MPPTCFG register, the master sends the value 0x01;

Slave sends an ACK;

Master sends a repeated start bit (Sr);

Master sends the address of the slave in 'read' mode;

Slave sends an ACK;

Master provides the clock on SCL to allow the slave to shift the data of the read register on SDA;

If the master wants to read register at the next address (STATUS.VOVDIS in our example), it sends an ACK and provides the clock for the slave to shift its following 8 bits of data. This can be done several times in a row for writing several registers;

If the master wants to end the transmission, it sends a NACK to notify the slave that the transmission is over, and then sends a stop bit (P).

Both communications are described in the figure 9. Refer to table 10 for all register addresses.



## 8.6. Registers Map

Address	Name	Bit	Field Name	Access	RESET	Description
0×00		[3:0]	MINOR	R	-	Chip ID
0,00	VERSION	[7:4]	MAJEUR	R	-	
0v01	MODICEC	[3:0]	RATIO	R/W	0x07 (85%)	MPPT ratio
0,01	MEETCIG	[6:4]	TIMING	R/W	0x07 (2ms/256ms)	MPPT timings
0x02	VOVDIS	[5:0]	THRESH	R/W	0x2D (3.05V)	Overdischarge level of the stor-
0/02	101013	[5.0]			0,20 (3.037)	age element
0x03	VOVCH	[5:0]	THRESH	R/W	0x33 (4.1V)	Overcharge level of the storage
0.04		[7.0]	TURECU	D /AA	0.0F (0°C)	element
0x04	TEMPCOLD	[7:0]	THRESH	R/W		
0x05	TEMPHOT	[7:0]	THRESH	R/W	0x2F (45 C)	Hot temperature level
		[0:0]	KEEPALEN	R/W	0x01	Keepalive enable
0x06	PWR	[1:1]	HPEN	R/W	0x01	
		[2:2]		R/W	0x01	Temperature monitoring enable
		[3:3]	STOCHDIS	R/W	0x00	Battery charging disable
0x07	SLEEP	[0:0]	EN	R/W	0x01	Sleep mode enable
000	CTOMON .	[3:1]	THRESH	R/W	0x00	
0x08	STOIVION	[2:0]	RATE	R/W	0x00	ADC rate
0.00	4514	[0:0]	EN	R/W	0x00	APM enable
0x09 APM	АРМ	[1:1]	MODE	R/W	0x00	APM mode
		[3:2]	WINDOW	R/W	0x00	APM computation window
		[0:0]	I2CRDY	R/W	0x01	IRQ serial interface ready enable
	IRQEN	[1:1]	VOVDIS	R/W	0x00	IRQ STO OVDIS enable
0x0A		[2:2]	VOVCH	R/W	0x00	IRQ STO OVCH enable
0.001		[3:3]	SLPTHRESH	R/W	0x00	IRQ SRC LOW enable
		[4:4]	TEMP	R/W	0x00	IRQ temperature enable
		[5:5]	APMDONE	R/W	0x00	IRQ APM done enable
		[0:0]	UPDATE	R/W	0x00	Configuration through I <sup>2</sup> C or
0x0B	CTRL	[0.0]		.,		configuration pins
		[2:2]	SYNCBUSY	R	0x00	Synchronization busy flag
		[0:0]	I2CRDY	R	0x00	IRQ serial interface ready flag
		[1:1]	VOVDIS	R	0x00	IRQ STOR OVDIS flag
0x0C	IROFIG	[2:2]	VOVCH	R	0x00	IRQ STOR OVCH flag
		[3:3]	SLPTHRESH	R	0x00	IRQ SRC LOW flag
		[4:4]	TEMP	R	0x00	IRQ temperature flag
		[5:5]	APMDONE	R	0x00	IRQ APM done flag
		[1:1]	VOVDIS	R	0x00	Status STO OVDIS
		[2:2]	VOVCH	R	0x00	Status STO OVCH
0x0D	STATUS	[3:3]	SLPTHRESH	R	0x00	Status SRC LOW
		[4:4]	TEMP	R	0x00	Status temperature
		[6:6]	CHARGE	R	0x00	Status STO CH
0x0E	APM0	[7:0]	DATA	R	0x00	APM data 0
0x0F	APM1	[7:0]	DATA	R	0x00	APM data 1
0x10	APM2	[7:0]	DATA	R	0x00	APM data 2
0x11	TEMP	[7:0]	DATA	R	0x00	Temperature data
0x12	STO	[7:0]	DATA	R	0x00	Battery voltage
0x13	SRC	[7:0]	DATA	R	0x00	SRC ADC value

Table 10: Register summary



## 8.7. Registers Configurations

#### 8.7.1. MPPT Register

The MPPT register is composed of 2 parts. The first part is reserved for the MPP ratio. This parameter is set on bits [3:0] of the register. The second part allows configuring the duration of the evaluation of  $V_{OC}$  and the time between two MPP evaluations. The configuration is set on bits [6:4] of the register. All the information about the MPPT are available on section 7.2.

#### 8.7.2. Storage Element Threshold Registers

The configuration of the storage element thresholds is done by setting two different registers through the  $\rm I^2C$  communication:

- The V<sub>OVDIS</sub> threshold is configured in register VOVDIS (0x02);
- The V<sub>OVCH</sub> threshold is configured in register VOVCH (0x03).

All the information about the storage element threshold voltage are available on section 8.4.

#### 8.7.3. Temperature Register

The configuration of the temperature thresholds is done by setting two registers through  $I^2C$  communication:

- The low temperature threshold is configured in register TEMPCOLD (0x04);
- The high temperature threshold is configured in register TEMPHOT (0x05).

The temperature protection uses a voltage divider consisting of the resistor Rdiv and the thermistor Rth. Considering the specifications of the thermistor used, it is possible to determine the relationship between the temperature and the resistance of the thermistor. The following equation must therefore be applied to determine the value to be written to the register:

$$THRESH = 256 \text{ x} \frac{\text{Rth}}{\text{Rth} + \text{Rdiv}}$$

The equation is the same for both the high and the low thresholds. THRESH is the value to be written to the registers,

Rth is the impedance of the thermistor at the threshold temperature and Rdiv is the resistance of the voltage divider as shown on figure 6. The AEM10900 determines if the ambient temperature is within the range previously set by measuring the voltage on pin TH\_MON.

For example with a Murata NCP15XH103J03RC the default thresholds are 0°C and 45°C (see table 10), which matches the specifications of most Li-Ion batteries.

#### 8.7.4. Power Register

The PWR (0x06) register is dedicated to the power settings of the AEM10900 and is made of 4 bits:

Bit [3]	Bit [2]	Bit [1]	Bit [0]
STOCHDIS	TMONEN	HPEN	KEEPALEN
0	1	1	1

Table 11: PWR Register

#### Bit [3]: Battery charging disable (PWR.STCHDIS).

This register is allowed in read and write mode.

Setting this bit to 0 allows the charging of the battery. Setting this bit to 1 disables it.

#### Bit [2]: Temperature monitoring enable (PWR.TMONEN).

The temperature monitoring enable bit enables the monitoring of the ambient temperature.

Setting this bit to 1 enables the temperature monitoring. Setting this bit to 0 disables it.

#### Bit [1]: High-power mode enable (PWR.HPEN).

Setting this bit to 1 allows the AEM to automatically enter high-power mode if needed, allowing for more power to be harvested from SRC (see section 7.5.).

Setting this bit to 0 disables automatic high-power mode.

#### Bit [0]: Keep alive enable (PWR.KEEPALEN).

This field defines the energy source from which the AEM10900 supplies VINT (internal circuitry).

When PWR.KEEPALEN is set to 0, VINT is supplied by SRC through the boost converter. When PWR.KEEPALEN field is set to 0, VINT is supplied by STO. Refer to section 7.6. for more informations.



#### 8.7.5. Sleep Register

The Sleep register enables the sleep mode and sets the conditions for entering the sleep mode.



Table 12: SLP register

#### Bit [3:1]: Sleep threshold (SLEEP.THRESH)

This field sets the voltage threshold below which the AEM10900 enters SLEEP STATE. Table  $13\ \text{shows the available settings.}$ 

For example, if the sleep threshold is set to 010, the AEM will go into SLEEP STATE if the source voltage drops below 0.255V at the MPP ratio ( $V_{MPP}$ ).

Configuration	Sleep threshold
000	0.105 V
001	0.202 V
010	0.255 V
011	0.3 V
100	0.36 V
101	0.405 V
110	0.51 V
111	0.6 V

Table 13: Configuration of the sleep threshold

#### Bit [0]: Sleep mode enable (SLEEP.EN)

This field enables SLEEP STATE when set to 1. When set to 0, the AEM10900 will never switch to SLEEP STATE. The sleep mode threshold is set to 112mV.

#### 8.7.6. Acquisition of STO Register

This field configures the acquisition rate of the STO ADC. Depending on the application, the source and the storage element, the user might want to increase the frequency of the acquisitions of the battery voltage, so that the acquisition rate is significantly faster than the expected voltage variation on the battery. Increasing this frequency increases the energy consumption of the AEM10900.

Configuration	Sampling rate
000	Every 1.024 s
001	Every 512 ms
010	Every 256 ms
011	Every 128 ms
100	Every 64 ms

Table 14: Acquisition rates for STO ADC

#### 8.7.7. APM Register

Average Power Monitoring (APM) allows for estimating the energy transferred from the source to the battery over a certain period of time.

Bit [3]	Bit [2]	Bit [1]	Bit [0]
		MODE	E
0	0	0	0



#### Bit [3:2]: APM computation window (APM.WINDOW)

This field is used to select the APM computation window. The energy transferred is integrated over this configurable time window.

Configuration	Computation window
00	128 ms
01	64 ms
10	32 ms

Table 16: Configuration of APM computation windows The MPP period must be at least twice longer than the APM computation window. If the user sets a value that doesn't comply with the previous condition, the AEM10900 will automatically change it to the largest compliant value.

#### Bit [1]: APM mode (APM.MODE)

The APM implements two modes:

- Pulse counter mode: the AEM10900 counts the number of current pulses drawn by the boost converter. This mode is enabled by setting the APM mode bit to 0;
- Power meter mode: the number of pulses during a period is multiplied by a value to obtain the energy that has been transferred taking into account the efficiency of the AEM10900. This mode is enabled by setting the APM mode bit to 1. (this section needs to be completed on next version)

#### Bit [0]: APM enable (APM.EN)

This field enables the APM feature. When the APM.EN field bit is set to 1, it is enabled. If APM.EN field is set to 0, the feature is disabled.

#### 8.7.8. IRQEN Register

For some applications, it is interesting to have an interruption flag triggered by specific conditions on the IRQ pin. This register enables those interrupts.

Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
APMDONE	TEMP	SLPTHRESH	лолсн	SIDVOV	I2CRDY
0	0	0	0	0	1

Table 17: IRQEN register

#### Bit [5]: IRQ APM done enable (IRQEN.APMDONE)

This bit enables the generation of an interrupt when new APM data is available.

When set to 0, the interrupt is disabled. When set to 1, the interrupt is enabled.

#### Bit [4]: IRQ temperature enable (IRQEN.TEMP)

This bit enables the generation of an interrupt when the temperature crosses the minimum or maximum temperature allowed to charge the battery (see section 8.6.3.).

When set to 1, the interrupt is enabled. When set to 0, the interrupt is disabled.

#### Bit [3]: IRQ SRC LOW enable (IRQEN.SLPTHRESH)

This bit enables the generation of an interrupt when the AEM10900 sleep mode crosses the sleep mode threshold, which is set in the SLEEP register .

When set to 1, the interrupt is enabled. When set to 0, the interrupt is disabled.

#### Bit [2]: IRQ STOR OVCH enable (IRQEN.VOVCH)

This bit enables the generation of an interrupt when the battery voltage crosses the  $\rm V_{\rm OVCH}$  threshold.

When set to 1, the interrupt is enabled. When set to 0, the interrupt is disabled.

#### Bit [1]: IRQ STOR OVDIS enable (IRQEN.VOVDIS)

This bit enables the generation of an interrupt when the storage element voltage crosses the  $\rm V_{\rm OVDIS}$  threshold.

When set to 1, the interrupt is enabled. When set to 0, the interrupt is disabled.

#### Bit [0]: IRQ serial interface ready enable (IRQEN.I2CRDY)

This bit enables the generation of an interrupt when the serial interface ( $I^2C$ ) is ready to communicate. This interrupt is activated by default. After a reset and before communicating through the  $I^2C$  interface, the user must check that the IRQ pin is set high, to make sure the AEM10900 is ready to communicate.

When set to 1, the interrupt is enabled. When set to 0, the interrupt is disabled.

#### 8.7.9. Control Register

The CTRL register is used to load the configuration done through the  $\rm l^2C$  interface. It includes two fields.

Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
					SYNCBUSY		UPDATE
0	0	0	0	0	0	0	0

Table 18: CTRL register

#### Bit [2]: Synchronization busy flag (CTRL.SYNCBUSY)

This field indicates whether the synchronization from the  $I^2C$  registers to the system registers is ongoing or not. After CTRL.UPDATE is set to 1, CTRL.SYNCBUSY is set while the registers written by  $I^2C$  communication are being copied to the controller registers. CTRL.SYNCBUSY is reset to 0 when the copy is done and both  $I^2C$  registers and controller registers are synchronized.

#### Bit [0]: Load configuration (CTRL.UPDATE)

This field is used to load all the  $I^2C$  registers to the system registers and thus controls which configuration is active between the configuration pins and  $I^2C$ . If the field is set to 0, the configuration pins will be used to configure the AEM10900. If it is set to 1, the configurations performed through  $I^2C$  communications are loaded.

#### 8.7.10. IRQFLG Register

The IRQFLG register contains all interrupt flags, corresponding to those enabled in the IRQEN register.

Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
APMDONE	TEMP	SLPTHRESH	лоисн	NOVDIS	I2CRDY
0	0	0	0	0	0

Table 19: IRQFLG register

#### Bit [5]: IRQ APM done Flag (IRQFLG.APMDONE)

This interrupt flag is set to 1 when a new APM data is available, if the corresponding interrupt source has been previously enabled. If this bit is 0, this interruption hasn't been triggered.

#### Bit [4]: IRQ temperature Flag (IRQFLG.TEMP)

This interrupt flag is set to 1 when the temperature crosses the minimum or maximum temperature (selected through the TEMPCOLD and TEMPHOT registers), if the corresponding interrupt source has been previously enabled. If this bit is 0, this interruption hasn't been triggered.

#### Bit [3]: IRQ SRC LOW Flag (IRQFLG.SLPTHRESH)

This interrupt flag is set to 1 when the source crosses the sleep voltage (selected through the SLEEP register), if the corresponding interrupt source has been previously enabled. If this bit is 0, this interruption hasn't been triggered.





#### Bit [2]: IRQ STOR OVCH Flag (IRQFLG.VOVCH)

This interrupt flag is set to 1 when the battery crosses the overcharge voltage (selected through the VOVCH register), if the corresponding interrupt source has been previously enabled. If this bit is 0, this interruption hasn't been triggered.

#### Bit [1]: IRQ STOR OVDIS Flag (IRQFLG.VOVDIS)

This interrupt flag is set to 1 when the battery crosses the overdischarge voltage (selected through the VOVDIS register), if the corresponding interrupt source has been previously enabled. If this bit is 0, this interruption hasn't been triggered.

#### Bit [0]: IRQ serial interface ready Flag (IRQFLG.I2CRDY)

This interrupt flag is set to 1 when the I<sup>2</sup>C interface is ready to communicate, if the corresponding interrupt source has been previously enabled. If this bit is 0, this interruption hasn't been triggered.

#### 8.7.11. STATUS Register

The STATUS register contains informations about the status of the AEM10900.

Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
	CHARGE		TEMP	SLPTHRESH	КОИСН	VOVDIS	
0	0	0	0	0	0	0	0

Table 20: CTRL register

#### Bit [6]: Status STOR CH (STATUS.CHARGE)

This status indicates whether the AEM is currently charging the battery or not. If this bit is set to 0, the storage element charging is disabled. If it is set to 1, the storage element charging is enabled.

#### Bit [4]: Temperature Status (STATUS.TEMP)

This bit is set to 1 if the ambient temperature is outside the range defined by the TEMPCOLD and TEMPHOT registers. It is set to 0 is the temperature is within this range.

#### Bit [3]: Status SRC LOW (STATUS.SLPTHRESH)

This status indicates whether the source voltage is higher or lower than the sleep level threshold. If the source voltage is higher than the sleep level then the field is set to 0, else the field is set to 1.

#### Bit [2]: Status STOR OVCH (STATUS.VOVCH)

This status indicates whether the battery is higher or lower than the overcharge level threshold. If the battery voltage

rises above Vovch then the field set to 1, else it is set to 0.

#### Bit [1]: Status STOR OVDIS (STATUS.VOVDIS)

This status indicates whether the battery is higher or lower than the overdischarge level threshold. If the battery voltage goes below Vovdis then the field set to 1, else it is set to 0.

#### 8.7.12. APM Data Register

The APM register contains APM data. Depending on the mode of the APM configured in the APM register, the data has to be processed differently.

 If the APM is used in pulse counter mode, the data will simply be distributed to the three registers below;

Register APM0							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
DATA[7:0]							



Register APM2							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
DATA[23:16]							

Table 21: APMx registers in pulse counter mode

- If the APM is used in power meter mode, the data and an offset will be used in order to recover the measurement. To determine the power value in nano-Joule the data must be bit-shifted to SHIFT bits (see table 22) and multiplied by a factor  $\alpha$  TBD. This will reduce the accuracy of the measurement.

Register APM0							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
DATA[7:0]							

Register APM1							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
DATA[15:8]							

Register APM2							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
	SHIFT	[3:0]			DATA[	19:16]	

Table 22: APMx registers in pulse counter mode



#### 8.7.13. Temperature data Register

This field contains the result of the ADC acquisition for the temperature monitoring. The voltage at the terminals of the voltage divider can be derived by applying the following equation, with Vref = 1 V:

$$Vth = \frac{Vref x THRESH}{256}$$

Or, in order to make a comparison with the table in the thermistor data sheet, it is possible to find the impedance of the thermistor:

 $Rth = Rdiv \ge \frac{THRESH}{256 - THRESH}$ 

#### 8.7.14. Battery data Register

This field contains the 8 bits result from the ADC acquisition of the battery voltage. To convert the result to Volts, the following equation is applied.

 $Vsto = \frac{4.8V \text{ x DATA}}{256}$ 



#### 8.7.15. SRC Register

This register contains data reflecting the voltage level at which the input of the AEM10900 is regulated, resulting from the MPPT evaluation. To convert this value in Volts refer to table 23.

SRC.D	ATA Va	lue				Voltage Level
0	0	0	1	0	1	0.10 V
0	0	0	1	1	0	0.11 V
0	0	0	1	1	1	0.12 V
0	0	1	0	0	0	0.14 V
0	0	1	0	0	1	0.16 V
0	0	1	0	1	0	0.17 V
0	0	1	0	1	1	0.19 V
0	0	1	1	0	0	0.20 V
0	0	1	1	0	1	0.22 V
0	0	1	1	1	0	0.23 V
0	0	1	1	1	1	0.25 V
0	1	0	0	0	0	0.27 V
0	1	0	0	0	1	0.28 V
0	1	0	0	1	0	0.30 V
0	1	0	0	1	1	0.32 V
0	1	0	1	0	0	0.35 V
0	1	0	1	0	1	0.38 V
0	1	0	1	1	0	0.41 V
0	1	0	1	1	1	0.44 V
0	1	1	0	0	0	0.47 V
0	1	1	0	0	1	0.50 V
0	1	1	0	1	0	0.53 V
0	1	1	0	1	1	0.56 V
0	1	1	1	0	0	0.59 V

Table 23: Source regulation configuration pins

SRC.D	ATA Va	lue				Voltage Level		
0	1	1	1	0	1	0.62 V		
0	1	1	1	1	0	0.65 V		
0	1	1	1	1	1	0.68 V		
1	0	0	0	0	0	0.71 V		
1	0	0	0	0	1	0.74 V		
1	0	0	0	1	0	0.77 V		
1	0	0	0	1	1	0.80 V		
1	0	0	1	0	0	0.83 V		
1	0	0	1	0	1	0.86 V		
1	0	0	1	1	0	0.89 V		
1	0	0	1	1	1	0.92 V		
1	0	1	0	0	0	0.95 V		
1	0	1	0	0	1	0.98 V		
1	0	1	0	1	0	1.02 V		
1	0	1	0	1	1	1.05 V		
1	0	1	1	0	0	1.08 V		
1	0	1	1	0	1	1.11 V		
1	0	1	1	1	0	1.14 V		
1	0	1	1	1	1	1.17 V		
1	1	0	0	0	0	1.20 V		
1	1	0	0	0	1	1.23 V		
1	1	0	0	1	0	1.26 V		
1	1	0	0	1	1	1.29 V		
1	1	0	1	0	0	1.32 V		
1	1	0	1	0	1	1.35 V		
1	1	0	1	1	0	1.38 V		
1	1	0	1	1	1	1.41 V		
1	1	1	0	0	0	1.44 V		
1	1	1	0	0	1	1.47 V		
1	1	1	0	1	0	1.50 V		

Table 23: Source regulation configuration pins



### 8.8. External Components

#### 8.8.1. Storage element

The storage element of the AEM10900 must be a rechargeable battery, whose size should be chosen so that its voltage does not fall below  $V_{OVDIS}$  even during occasional current peak from the battery. To keep the chip functionality, minimum voltage on STO pin shall never fall below 2.8V.

The monitoring of the storage element is done periodically. It is therefore possible that the storage element may be overloaded if it is incorrectly sized.

It is advisable to buffer the battery with a capacitor if the internal resistance of the battery is high, to ensure that the current pulled from the battery by the application circuit does not ever make the battery voltage fall below 2.8 V.

If a disconnection of the battery is expected (e.g. because of a user removable connector), the PCB should include a decoupling capacitor to avoid over-voltage and under-voltage during that battery disconnection.

#### 8.8.2. External inductor information

The AEM10900 operates with one standard miniature inductor. LDCDC must sustain a peak current of at least 1 A and a switching frequency of at least 10 MHz. Low equivalent series resistance (ESR) strongly influence the power conversion efficiency of the DCDC converter. The

recommended value is 4.7  $\mu$ H.

#### 8.8.3. External capacitors information

#### CSRC

This capacitor acts as an energy buffer at the input of the boost converter. It prevents large voltage variations when the buck-boost converter is active. The recommended value is 10  $\mu$ F.

#### CINT

This capacitor acts as an energy buffer for the internal voltage supply. The recommended value is 3.3  $\mu F.$ 

#### 8.8.4. Optional external component for thermal monitoring

The following components are required for the thermal monitoring:

- One resistor, typ. 22 kΩ ±20% (PNRC0402FR-0722KL)
- One NTC thermistor, typ. R0 = 10 k $\Omega$  ±5% and Beta = 3380 K ±3% (NCP15XH103J03RC)

#### 8.8.5. Optional pull-up resistors for the I<sup>2</sup>C interface

SDA and SCL must be pulled-up by resistors (1 k $\Omega$ ) if the I<sup>2</sup>C interface is used. The value must be determined according to the I<sup>2</sup>C mode used.



## 9. Typical Application Circuits

## 9.1. Example Circuit 1



Figure 10: Typical application circuit 1

The circuit is an example of a system with solar energy harvesting with the AEM10900 (Package WLCSP16). It uses a Li-ion rechargeable battery as energy storage.

- Energy source: PV cell
- R\_MPP[0] = H: The MPP ratio is set to 80%
- T\_MPP[1:0]: VOC timing: 2 ms; MPP evaluation period: 256 ms
- STO\_CFG[2:0]: The storage element is a Li-ion battery

- V<sub>OVCH</sub> = 4.12 V
- V<sub>OVDIS</sub> = 3.01 V
- The thermal monitoring is used with a default threshold value (TEMP\_COLD = 0°C, TEMP\_HOT = 45°C) with Rdiv = 22kOhm and Rth: NCP15XH103J03RC.
- The I<sup>2</sup>C communication is not used.
- DIS\_STO\_CH is connected to GND: The charging of the storage element on STO is enabled



### 9.2. Example Circuit 2



Figure 11: Typical application circuit 2

The circuit is a example of a system with solar energy harvesting with the AEM10900 (Package WLCSP16). It uses a NiCd 3 cells battery as storage element. Before to configure the registers, the AEM have the same configuration as the example circuit 1.

- Energy source: PV cell
- R\_MPP[2:0]: Configured through the I<sup>2</sup>C communication (MPP ratio = 90%)
- T\_MPP[1:0]: Configured through the I<sup>2</sup>C communication (MPP timing = 2ms/128ms)
- STO\_CFG[2:0]: Configured through the I<sup>2</sup>C
  communication
- V<sub>OVCH</sub> = 4.12 V
- V<sub>OVDIS</sub> = 3.30 V

- The thermal monitoring is used and the thresholds are configured through the I<sup>2</sup>C communication (Cold threshold = 10 °C, Hot threshold = 60 °C with Rdiv = 22kOhm and Rth: NCP15XH103J03RC.)
- DIS\_STO\_CH is connected to GND: The charging of the storage element on STO is enabled

Register	Value
0x01	1010001
0x02	110010
0x03	110011
0x04	01110100
0x05	00011111

Note: A configuration tool is available on the website. It helps the user to read and write on the register.





STO\_CFG[2:0] = HHH, R\_MPP[2:0] = LHH, T\_MPP[1:0] = HL, storage element: capacitor (10mF) pre-charged to 3V, SRC: current source 5mA with voltage compliance (0.8V), DIS\_STO\_CH = GND, KEEP\_ALIVE = H.



STO\_CFG[2:0] = HHH, R\_MPP[2:0] = LHH, T\_MPP[1:0] = HL, storage element: capacitor (10mF) pre-charged to 3V, SRC: current source 5mA with voltage compliance (0.8V), DIS\_STO\_CH = GND, KEEP\_ALIVE = H.





Figure 14: Behavior with the Keep Alive mode and without the source

8

10

12

14

6

2

4

STO\_CFG[2:0] = HHH, R\_MPP[2:0] = LHH, T\_MPP[1:0] = HL, storage element: capacitor (10mF) pre-charged to 3V, SRC: current source 5mA with voltage compliance (0.8V)(stop after ~4.5sec), DIS\_STO\_CH = GND, KEEP\_ALIVE = H.



Figure 15: Behavior without the Keep Alive mode and without the source

STO\_CFG[2:0] = HHH, R\_MPP[2:0] = LHH, T\_MPP[1:0] = HL, storage element: capacitor (10mF) pre-charged to 3V, SRC: current source 5mA with voltage compliance (0.8V)(stop after ~5sec), DIS\_STO\_CH = GND, KEEP\_ALIVE = H.

AEM10900







STO\_CFG[2:0] = HHH, R\_MPP[2:0] = LHH, T\_MPP[1:0] = HL, storage element: capacitor (10mF) pre-charged to 3V, SRC: current source 5mA with voltage compliance (0.8V)(stop after ~5sec), DIS\_STO\_CH = GND, KEEP\_ALIVE = H. The temperature is lower than 0°C before 6.5s and after 13.2s.









**10. Performance Data** 10.1. DCDC Conversion Efficiency



Figure 17: DCDC Conversion Efficiency (LDCDC: VLS252012HBX-4R7M-1)

### 10.2. Quiescent Current



Figure 18: Quiescent Current



## 11. Package Information

11.1. Wafer Level Chip Scale Package (WLCSP16 2x2mm)





#### 11.2. WLCSP16 Board Layout



Figure 20: WLCSP16 board layer





### 11.3. Plastic quad flatpack no-lead (QFN28 4x4mm)





11.4. QFN28 Board Layout



Figure 22: QFN28 4x4 mm board layout



#### 11.5. Minimum BOM



#### Figure 23: AEM10900 schematic

	Designator	Description	Quantity	Manufacturer	Part Number	
/	U1	AEM10900	1	e-peas	order at sales@e-peas.com	
tor	Battery	Battery with 2.8 V min. voltage	1	To be defined by user		
Idat	LDCDC	Power inductor 4.7 μH 1.9A 1008	1	TDK	VLS252012HBX-4R7M-1	
Jar	CSRC	Ceramic capacitor 22 µF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01	
2	CINT	Ceramic capacitor 22 µF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01	
_	RZMPP	Resistor for ZMPP functionality	1	To be defined by	user	
ona	R1, R2	Pull-up 1kΩ Resistors for I <sup>2</sup> C interface	2	Yageo	AC0603FR-071KL	
pti	Rth	$10k\Omega$ NTC thermistor for temperature monitoring	1	Murata	NCP15XH103J03RC	
0	Rdiv	Resistor 22kΩ 1%	1	Yageo	PNRC0402FR-0722KL	

Table 24: AEM10900 bill of material



# 12. Revision History

Revision	Date	Description
1.0	April, 2021	Creation of the document.
1.1	April, 2021	p23 → Modification of the table 23: SRC_DATA register value Section 10. Performance: added Section 9. Typical Apllication circuits: added
1.2	August, 2022	Change name of the register and field for the I <sup>2</sup> C Communication Change the Package and the pinout for the WLCSP package